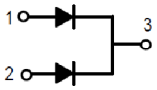
Super Fast Recovery Diode, 400A

Features

- Dual Diode Construction
- Low Leakage Current
- Low forward voltage drop
- High surge current capability
- Super Fast Switching





TWIN TOWER PACKAGE

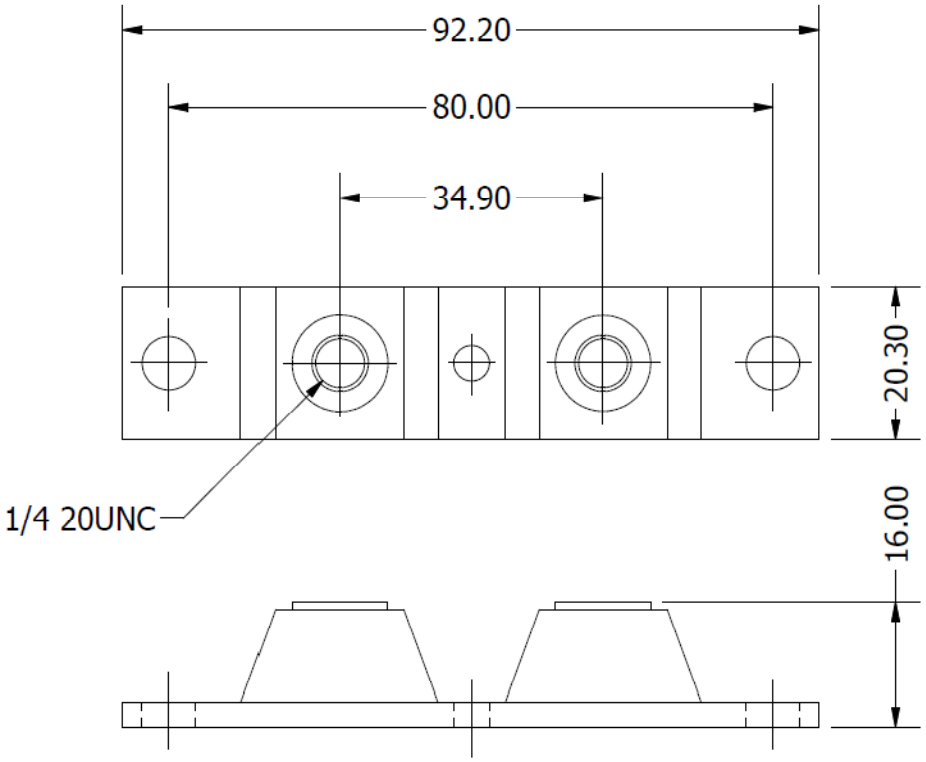
Maximum Ratings (T_J = 25°C unless otherwise specified)						
Parameter	**Symbol**	**Conditions**	**MUR40005CT(R)**	**MUR40010CT(R)**	**MUR40020CT(R)**	**Units**
Repetitive peak reverse voltage	V_{RRM}		50	100	200	V
RMS reverse voltage	V_{RMS}		35	70	140	V
DC blocking voltage	V_{DC}		50	100	200	V
Average forward current	$I_{F(AV)}$	$T_C \leq 125$ °C	400	400	400	A
Non-repetitive forward surge current, half sine-wave	I_{FSM}	T_C = 25 °C	2400	2400	2400	A

Electrical Characteristics (T_J = 25°C unless otherwise specified)						
Parameter	**Symbol**	**Conditions**	**MUR40005CT(R)**	**MUR40010CT(R)**	**MUR40020CT(R)**	**Units**
DC forward voltage	V_F	I_F = 125 A T_J = 25 °C	1.3	1.3	1.3	V
DC reverse current	I_R	V_R = 50 V T_J = 25 °C	25	25	25	µA
		V_R = 50 V T_J = 125°C	3	3	3	mA
Maximum Reverse Recovery Time	t_{rr}	I_F = 0.5A I_R = 1.0A I_{RR} = 0.25A	90	90	90	nS

Thermal Characteristics (T_J = 25°C unless otherwise specified)						
Parameter	**Symbol**		**MUR40005CT(R)**	**MUR40010CT(R)**	**MUR40020CT(R)**	**Units**
Thermal resistance junction to case	R_{thJ-C}		0.14	0.14	0.14	°C/W
Operating, storage temperature range	T_J , T_{stg}		- 40 to +175	- 40 to +175	- 40 to +175	°C

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Package Outline



ALL DIMENSIONS IN MM

Ordering Table

MUR	*400*	*05*	*CT*
1	2	3	4

1 – Device Type
- MUR = Dual Diode Recovery Module

2 – Current Rating = $I_{F(AV)}$

3 – Voltage = code x 10 = V_{RRM}

4 – Polarity
- CT = Normal (Cathode to Base)
- CTR = Reverse (Anode to Base)

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